Please amend the paragraph beginning on Page 8, line 3, to read as follows:

A2

Such a deterioration of a light-emitting diode will be described with reference to Figure 11. Figure 11 shows the light-emitting diode **200** previously described with reference to Figure **8**, but in a deteriorated condition. Since like components are designated with like reference numerals, the explanations thereof are omitted here.

Please amend the paragraph beginning on Page 18, line 22, to read as follows:

A3

Although the above descriptions are related to the case where the GaAs substrate is employed, the similar effects can be obtained with any other appropriate substrates, such as a GaP substrate, an InP substrate and the like. In the case where there is no limit to a material for the substrate, the lattice mismatch between the $(Al_xGa_{1-x})_yIn_{1-y}P$ current diffusion layer and the substrate may become about 8% at most with the variation of the In mole fraction. However, such a lattice mismatch will not have a significant effect on a resistivity of a bulk material.

Please amend the paragraph beginning on Page 19, line 11, to read as follows:

A4

As described above, although the lattice mismatching is generated between the $(Al_xGa_{1-x})_yIn_{1-y}P$ current diffusion layer and the underlying light-emitting structure by decreasing the In mole fraction of the constituting material for the current diffusion layer, this will not have significant disadvantages on the characteristics of a resultant light-emitting diode. Thus, by decreasing the In mole fraction of the $(Al_xGa_{1-x})_yIn_{1-y}P$ current diffusion layer to increase an absolute value of a lattice mismatch in the negative phase, the resistivity of the $(Al_xGa_{1-x})_yIn_{1-y}P$ current diffusion layer can be reduced. Accordingly, by decreasing the In mole fraction 1-y as well as the Al mole fraction x of the $(Al_xGa_{1-x})_yIn_{1-y}P$ current diffusion layer so that the current diffusion layer becomes intentionally lattice-mismatching with the light-emitting structure, the resistivity of the

A4

$(Al_xGa_{1-x})_yIn_{1-y}P$ current diffusion layer can be prescribed at the same level as that of the conventional AlGaAs current diffusion layer. Thus, it becomes possible to form the satisfactory current diffusion layer even by using the $(Al_xGa_{1-x})_yIn_{1-y}P$ layer.

Please amend the paragraph beginning on page 35, line 13 to read as follows:

A5

Light emitted from a portion of the light-emitting structure **11** right below the p-type electrode **8** cannot be taken out since it is blocked by the electrode **8**. Thus, by providing the current blocking layer **9** in the lower portion of the graded current diffusion layer **106** so as to be positioned right below the p-type electrode **8**, a current to be injected into the light-emitting structure **11** is allowed to be effectively spread so as to not flow in the portion right below the p-type electrode **8**. Thus, the light-emission from the portion right below the p-type electrode **8** is prevented. Accordingly, an invalid current which otherwise flows into the portion right below the p-type electrode **8** is reduced, and a light-emission efficiency can be improved.

Please amend the paragraph beginning on page 38, line 5 to read as follows:

A6

It is understood from Figure **7B** that since the Al and In mole fractions are high in an initial growth stage, the graded $(Al_xGa_{1-x})_yIn_{1-y}P$ current diffusion layer **106** shows a resistivity substantially the same as that of the light-emitting structure **11**. However, the Al and In mole fractions are decreased with the increase in the thickness, so that a resistivity is also decreased. It should be noted that in the light-emitting diode **150** provided with the current blocking layer **9**, a current is more likely to be spread throughout the whole chip through a portion of the current diffusion layer **106** which has a lower resistivity positioned closer to the p-type electrode **8**, whereby an operating voltage is less likely to be increased. On the other hand, even when a resistivity of the current diffusion layer **106** in a portion closer to the light-emitting structure **11** is